

# EL - 6F11

The EL - 6F11 is a high - power GaAs IRED mounted in a clear epoxy package. This IRED is both compact and easy to mount.

## FEATURES

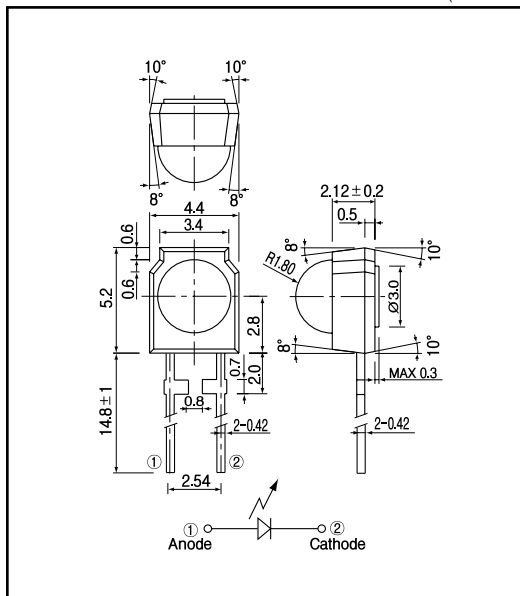
- Plastic mold package with a large caliber lens
- High output power

## APPLICATIONS

- Optical switches

## DIMENSIONS

(Unit : mm)



## MAXIMUM RATINGS

(Ta=25 )

Item	Symbol	Rating	Unit
Reverse voltage	$V_R$	4	V
Forward current	$I_F$	50	mA
Power dissipation	$P_D$	80	mW
Pulse forward current <sup>*1</sup>	$I_{FP}$	1	A
Operating temp.	Topr.	- 25 +85	
Storage temp.	Tstg.	- 40 +85	
Soldering temp. <sup>*2</sup>	Tsol.	260	

\*1. pulse width :  $t_w$  100  $\mu$ sec.period :  $T=10$ msec.

\*2. For MAX.5 seconds at the position of 2 mm from the package

## ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25 )

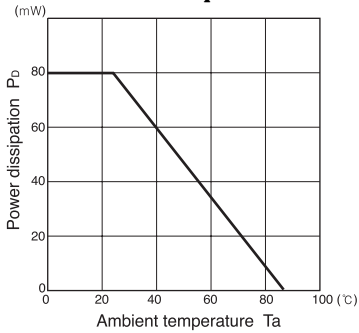
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	$V_F$	$I_F=50$ mA		1.3	1.65	V
Reverse current	$I_R$	$V_R=4$ V			10	$\mu$ A
Peak emission wavelength	$\lambda_p$	$I_F=20$ mA		940		nm
Spectral bandwidth		$I_F=20$ mA		50		nm
Radiant intensity <sup>*3</sup>	$P_D$	$I_F=50$ mA	2.5	6.0		V
Half angle		$I_F=20$ mA		$\pm 25$		deg.

\*3. Measured by tester of KODENSHI CORP.

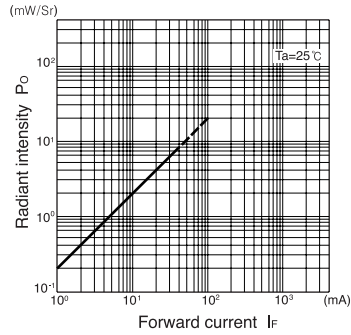
# Infrared Emitting Diodes(GaAs)

## EL - 6F11

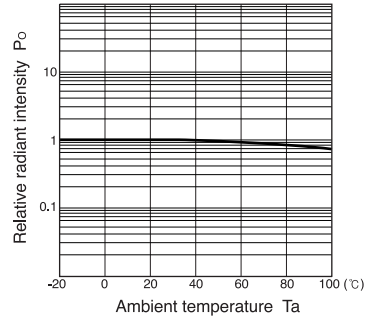
**Power dissipation Vs. Ambient temperature**



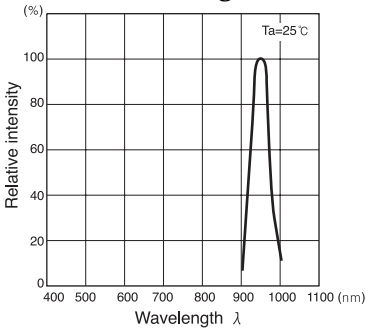
**Radiant intensity Vs. Forward current**



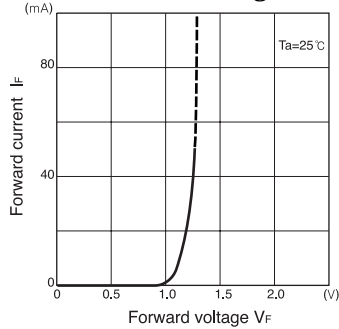
**Relative radiant intensity Vs. Ambient temperature**



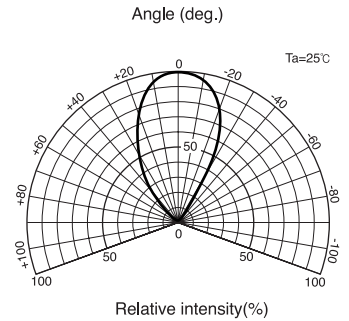
**Relative intensity Vs. Wavelength**



**Forward current vs. Forward voltage**



**Radiant Pattern**



**Relative radiant intensity Vs. Distance**

